ITP03N80A
ITA03N80A

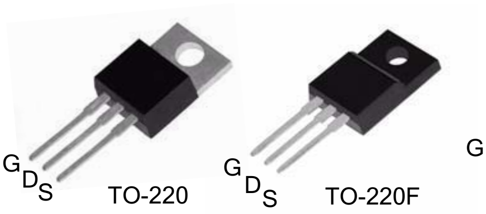
N-Channel MOSFET

Lead Free Package and Finish

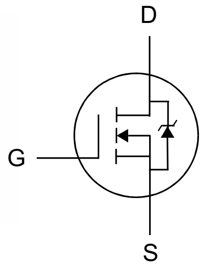
Applications:
- CRT, TV/Monitor
- Other Applications

V_{DSS}	$R_{DS(ON)}$ (Typ.)	I_D
800 V	3.8 Ω	3.0 A

Features:
- RoHS Compliant
- Low ON Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve



Packages
Not to Scale



Ordering Information

PART NUMBER	PACKAGE	BRAND
ITP03N80A	TO-220	***IPS***
ITA03N80A	TO-220F	***IPS***

Absolute Maximum Ratings T_C=25 °C unless otherwise specified

Symbol	Parameter	ITP03N80A	ITA03N80A	Units
V_{DSS}	Drain-to-Source Voltage (NOTE *1)	800		V
I_D	Continuous Drain Current	3.0	3.0	A
I_D@ 100 °C	Continuous Drain Current	Figure 3		A
I_{DM}	Pulsed Drain Current, V_{GS}@ 10V (NOTE *2)	Figure 6		A
P_D	Power Dissipation	85	28	W
	Derating Factor above 25 °C	0.68	0.22	W/°C
V_{GS}	Gate-to-Source Voltage	± 30		V
E_{AS}	Single Pulse Avalanche Engergy L=10 mH	150		mJ
I_{AS}	Pulsed Avalanche Rating	Figure 8		A
dv/dt	Peak Diode Recovery dv/dt (NOTE *3)	5.0		V/ns
T_L T_{PKG}	Maximum Temperature for Soldering Leads at 0.063 in (1.6 mm) from Case for 10 seconds Package Body for 10 seconds	300 260		°C
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150		°C

** Drain Current Limited by Maximum Junction Temperature*

***Caution:** Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.*

Thermal Resistance

Symbol	Parameter	ITP03N80A	ITA03N80A	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	1.47	4.46	°C/W	Drain lead soldered to water cooled heatsink, P_D adjusted for a peak junction temperature of +150 °C.
$R_{\theta JA}$	Junction-to-Ambient	62	100	°C/W	1 cubic foot chamber, free air.

OFF Characteristics T_J=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	800	--	--	V	V_{GS}=0V, I_D=250μA
$\Delta BV_{DSS}/\Delta T_J$	BreakdownVoltage Temperature Coefficient, Figure 11.	--	0.61	--	V/°C	Reference to 25°C, I_D=250μA
I_{DSS}	Drain-to-Source Leakage Current	--	--	1.0	μA	V_{DS}=800V, V_{GS}=0V
		--	--	125		V_{DS}=640V, V_{GS}=0V T_J=125°C
I_{GSS}	Gate-to-Source Forward Leakage	--	--	100	nA	V_{GS}=+30V
	Gate-to-Source Reverse Leakage	--	--	-100		V_{GS}= -30V

ON Characteristics T_J=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance Figure 9 and 10.	--	3.8	4.8	Ω	V_{GS}=10V, I_D=1.5A (NOTE *4)
$V_{GS(TH)}$	Gate Threshold Voltage, Figure 12.	2.0	--	4.0	V	V_{DS}=V_{GS}, I_D=250μA
gfs	Forward Transconductance	--	5.5	--	S	V_{DS}=15V, I_D=3.0A (NOTE *4)

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
C_{iss}	Input Capacitance	--	480	--	pF	V_{GS}=0V V_{DS}=25V f =1.0MHz Figure 14
C_{oss}	Output Capacitance	--	45	--		
C_{rss}	Reverse Transfer Capacitance	--	23	--		
Q_g	Total Gate Charge	--	15	--	nC	V_{DD}=400V I_D=3.0A, Vgs=10V Figure 15
Q_{gs}	Gate-to-Source Charge	--	2.5	--		
Q_{gd}	Gate-to-Drain ("Miller") Charge	--	6.0	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	9.0	--	ns	V_{DD}=400V I_D=3.0A V_{GS}=10V R_G=12Ω
t_{rise}	Rise Time	--	9.0	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	32	--		
t_{fall}	Fall Time	--	14	--		

Source-Drain Diode Characteristics T_C=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	--	--	3.0	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	12	A	
V_{SD}	Diode Forward Voltage	--	--	1.5	V	I_S=3.0A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	140	--	ns	V_{GS}=0V I_F=3.0A, di/dt=100 A/µs
Q_{rr}	Reverse Recovery Charge	--	450	--	nC	

Notes:

*1. T_J = +25°C to +150°C.

*2. Repetitive rating; pulse width limited by maximum junction temperature.

*3. I_{SD}= 3.0 A, di/dt ≤ 100 A/µs, V_{DD} ≤ BV_{DSS}, T_J=+150°C.

*4. Pulse width ≤ 380µs; duty cycle ≤ 2%.

Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case

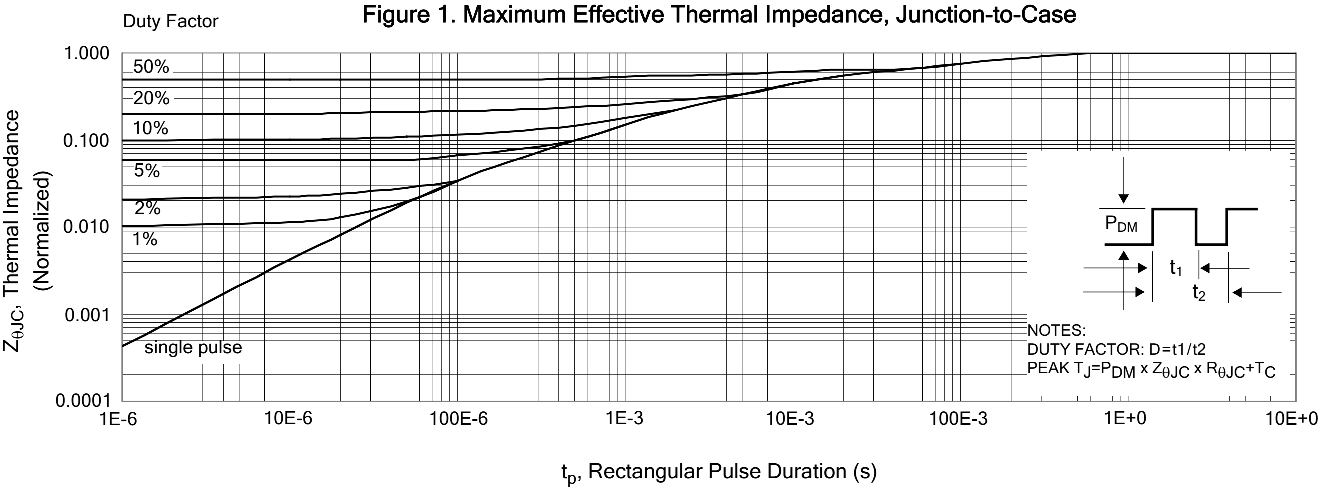


Figure 2. Maximum Power Dissipation vs Case Temperature

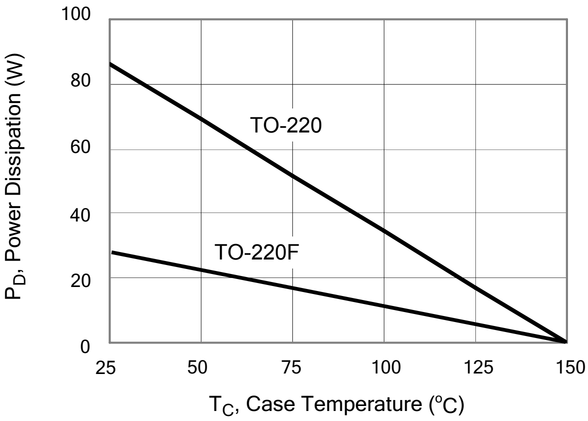


Figure 3. Maximum Continuous Drain Current vs Case Temperature

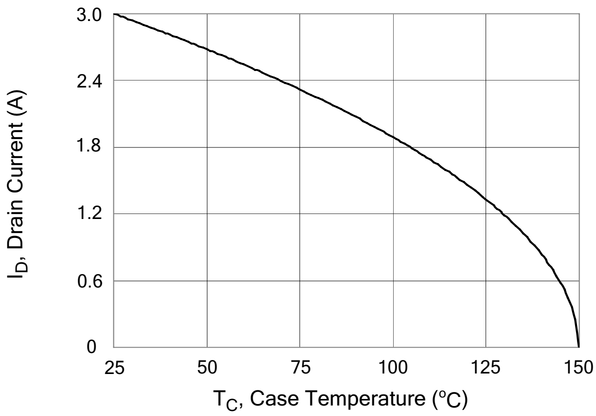


Figure 4. Typical Output Characteristics

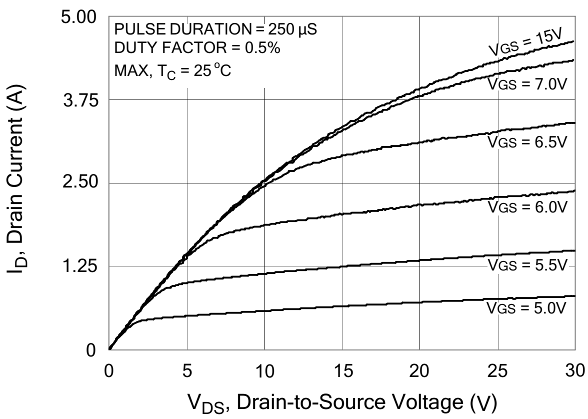


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

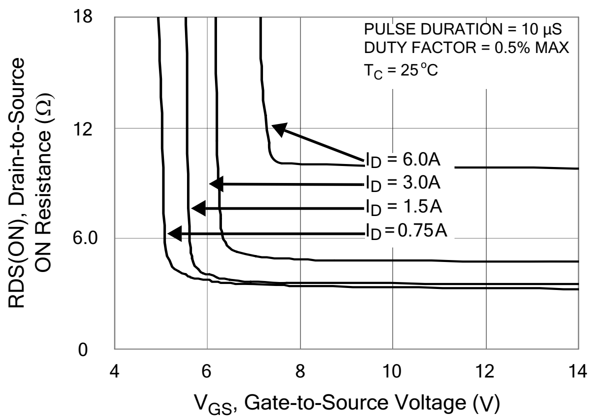


Figure 6. Maximum Peak Current Capability

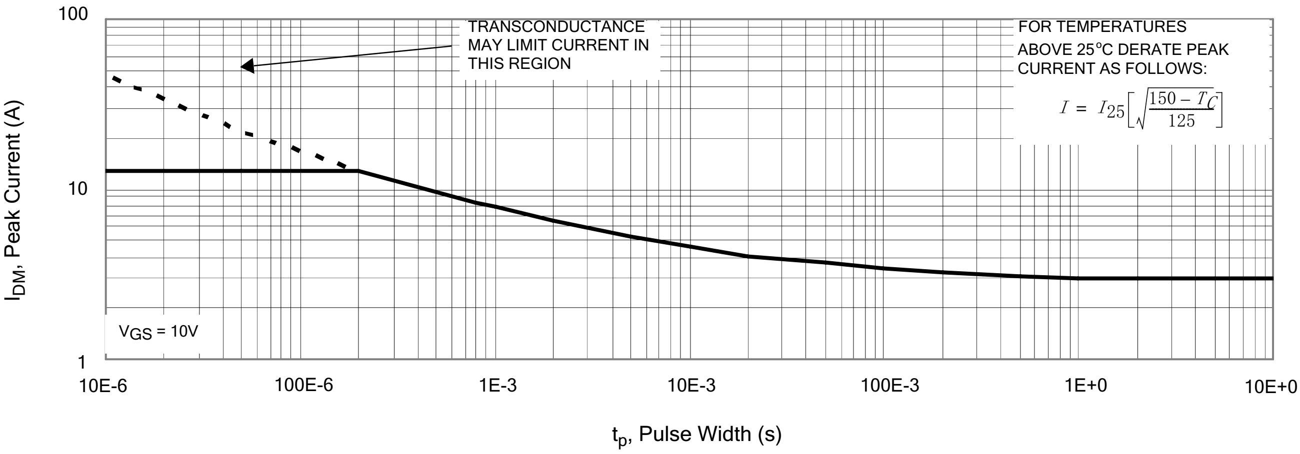


Figure 7. Typical Transfer Characteristics

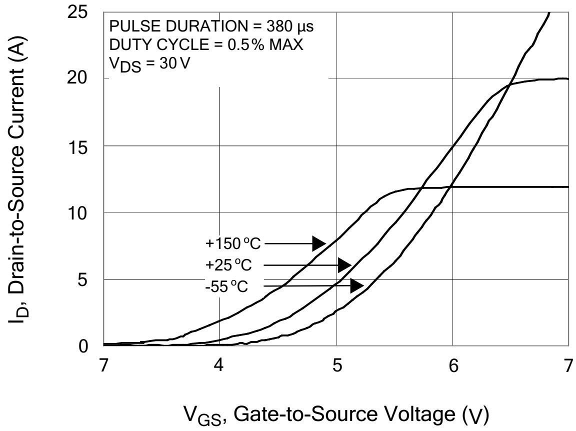


Figure 8. Unclamped Inductive Switching Capability

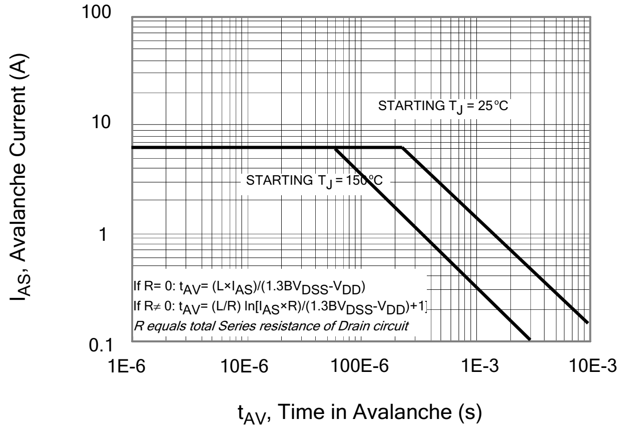


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

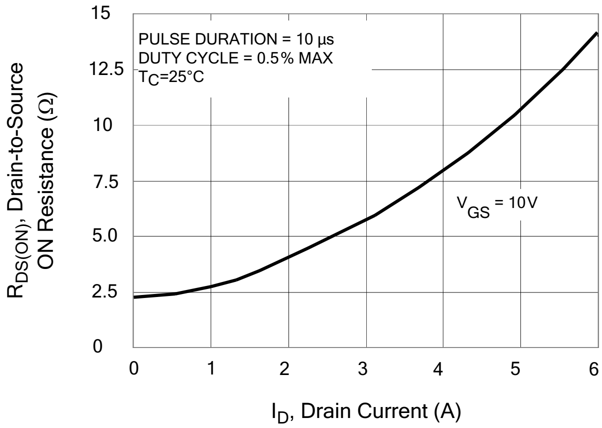


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

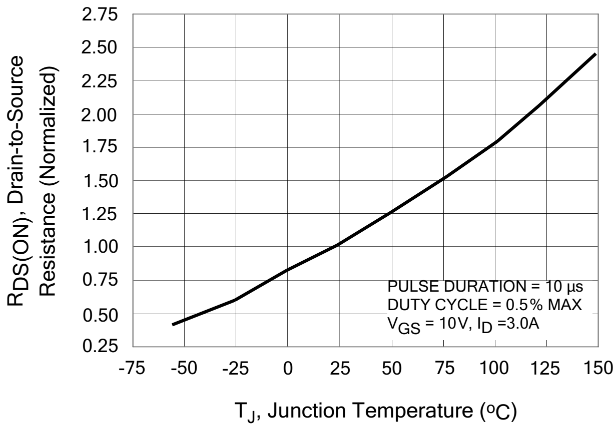


Figure 11. Typical Breakdown Voltage vs Junction Temperature

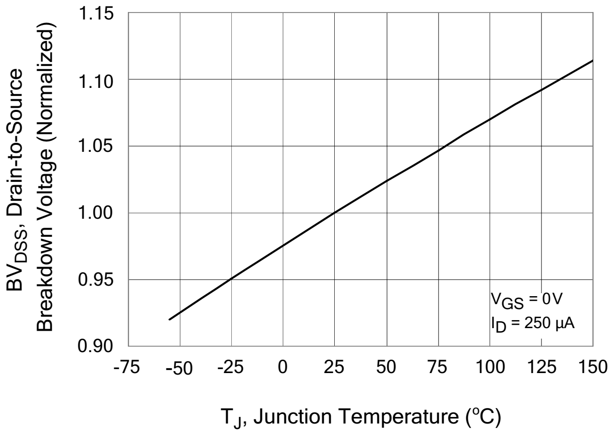


Figure 12. Typical Threshold Voltage vs Junction Temperature

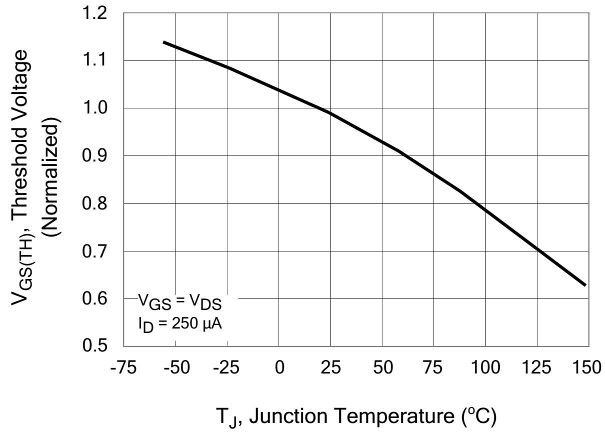


Figure 13. Maximum Forward Bias Safe Operating Area

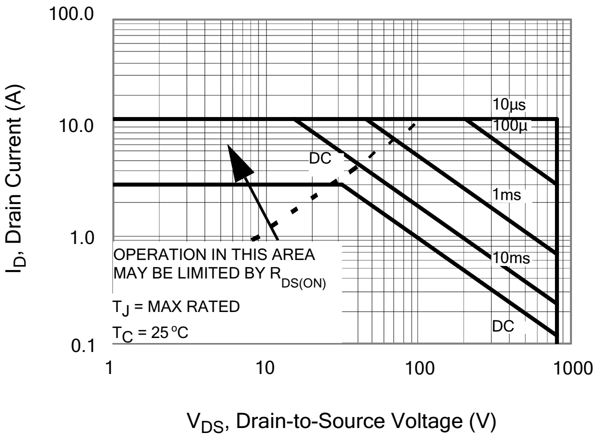


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

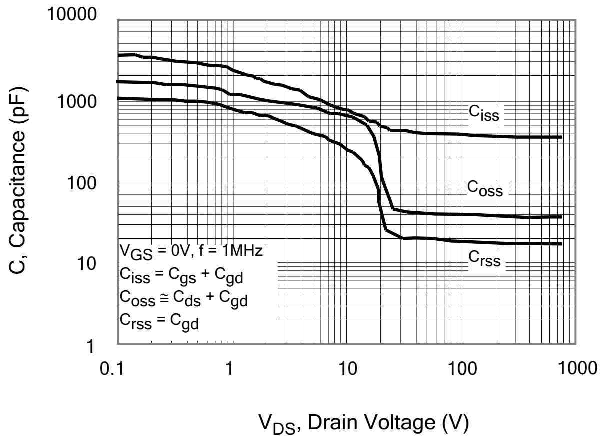


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

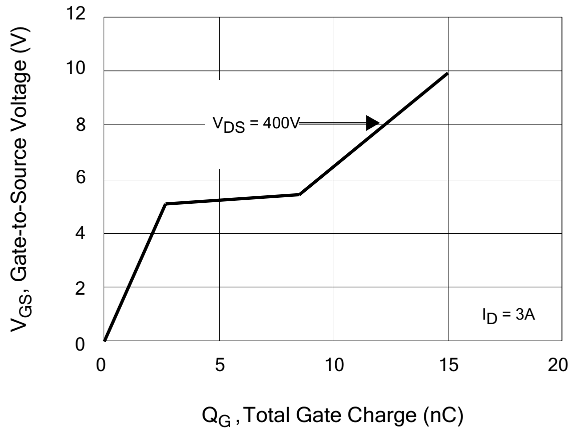
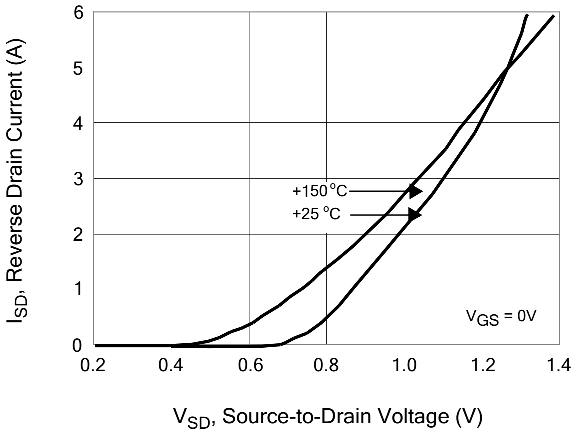


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

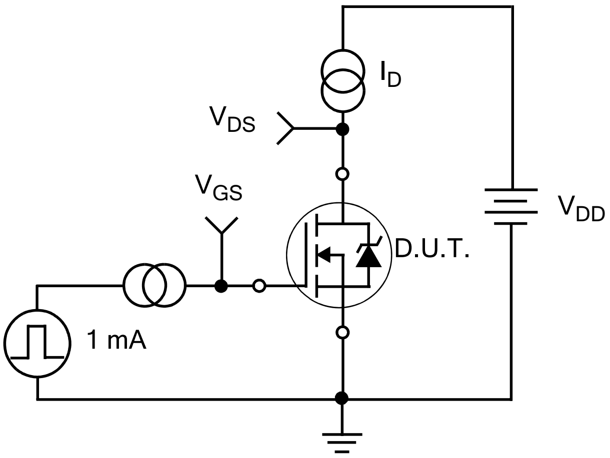


Figure 17. Gate Charge Test Circuit

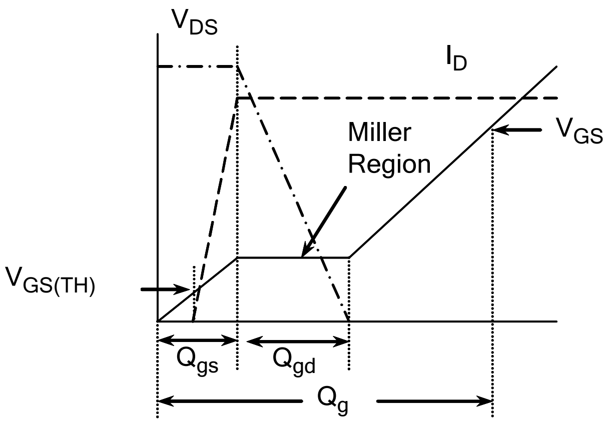


Figure 18. Gate Charge Waveform

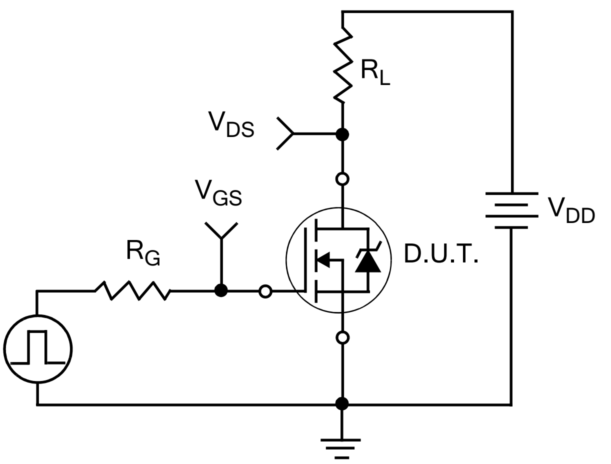


Figure 19. Resistive Switching Test Circuit

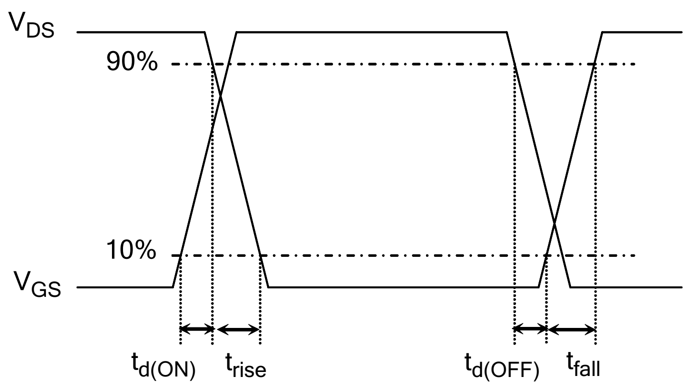


Figure 20. Resistive Switching Waveforms

Test Circuits and Waveforms

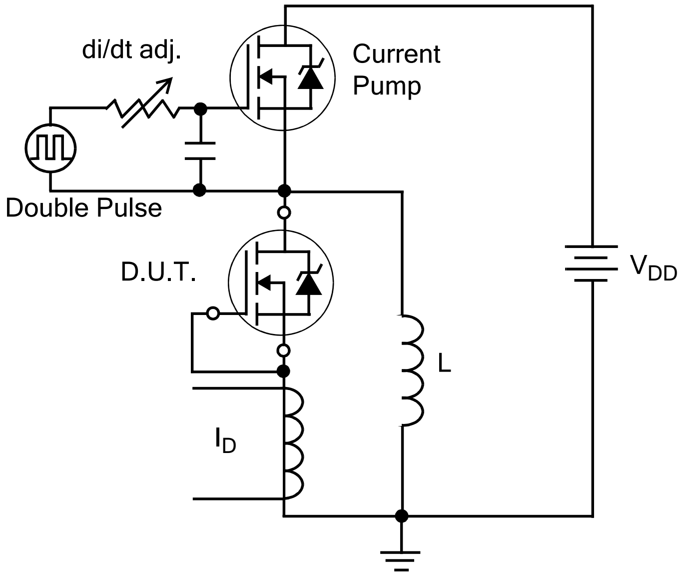


Figure 21. Diode Reverse Recovery Test Circuit

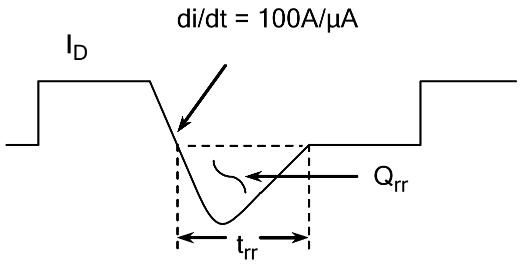


Figure 22. Diode Reverse Recovery Waveform

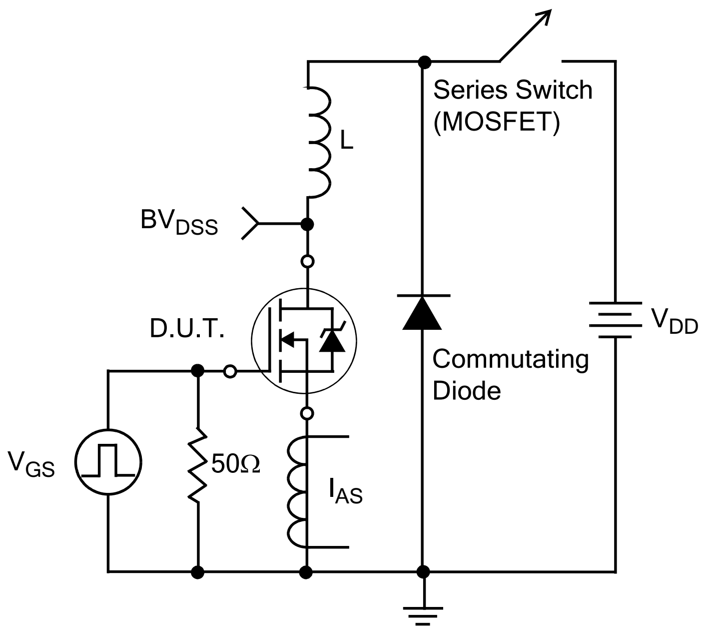
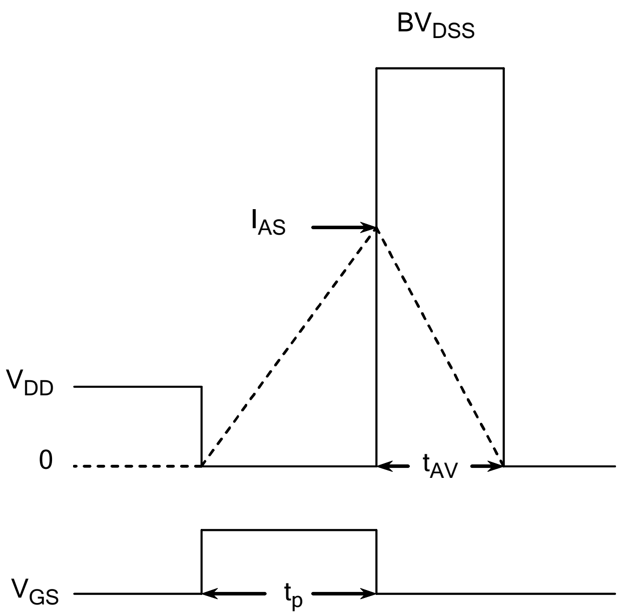


Figure 23. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Figure 24. Unclamped Inductive Switching Waveforms

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